Quad Operational Amplifier

HITACHI

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Description

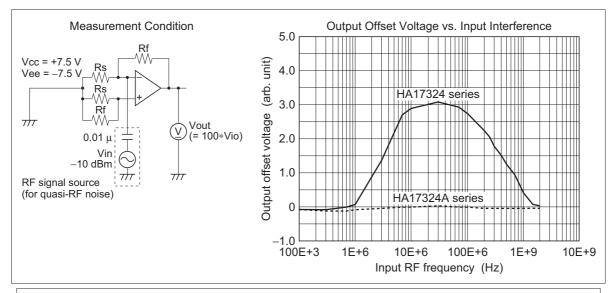
HA17324 series and HA17324A series are quad operational amplifier that provide high gain and internal phase compensation, with single power supply. They can be widely used to control equipments.

Features

- Wide range of supply voltage, and single power supply used
- Internal phase compensation
- Wide range of common mode voltage, and possible to operate with an input about 0V

Features only for "A" series

• Low electro-magnetic interference level



Notice: The example of an applied circuit or combination with other equipment shown herein indicates characteristics and performance of semiconductor -applied products.

The company shall assume no responsibility for any problem involving a patent caused when applying the descriptions in the example.



Ordering Information

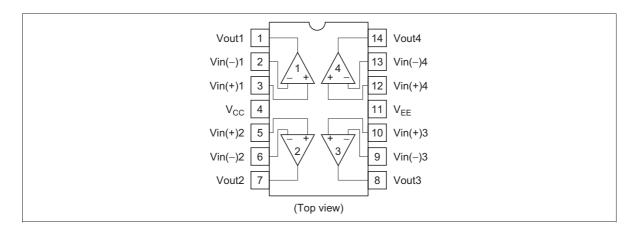
HA17324 Series

Type No.	Application	Package	
HA17324P	Industrial use	DP-14	
HA17324FP		FP-14DA	
HA17324	Commercial use	DP-14	
HA17324F		FP-14DA	

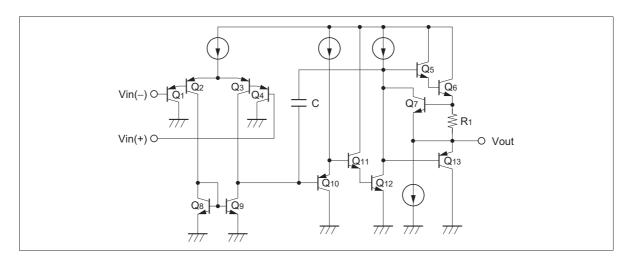
HA17324A Series

Type No.	Application	Package
HA17324AP	Industrial use	DP-14
HA17324ARP	_	FP-14DN
HA17324AFP	_	FP-14DA

Pin Arrangement



Circuit Schematic (1/4)



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

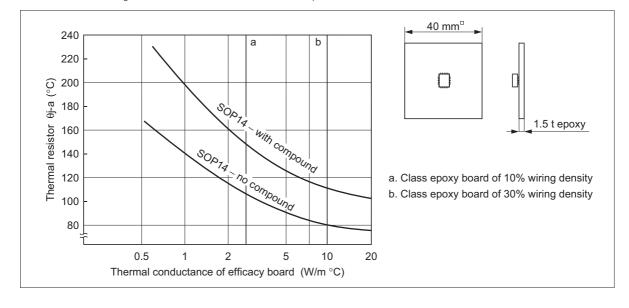
		Ratings			
Item	Symbol	HA17324/P/AP	HA17324F/FP/ARP/AFP	Unit	
Supply voltage	V _{cc}	32	32	V	
Sink current	Isink	50	50	mA	
Power dissipation	P _T	625 * ¹	625 * ²	mW	
Common mode input voltage	V _{CM}	-0.3 to V_{CC}	–0.3 to $V_{\rm cc}$	V	
Differential input voltage	Vin (diff)	$\pm V_{cc}$	$\pm V_{\tt CC}$	V	
Operating temperature	Topr	-20 to +75	–20 to +75	°C	
Storage temperature	Tstg	-55 to +125	-55 to +125	°C	

Notes: 1. This is the allowable values up to Ta = 50° C. Derate by 8.3 mW/°C.

2. Tjmax = θ j-a · P_cmax + Ta (θ j-a; Thermal resistor between junction and ambient at set board use).

The wiring density and the material of the set board must be chosen for thermal conductance of efficacy board.

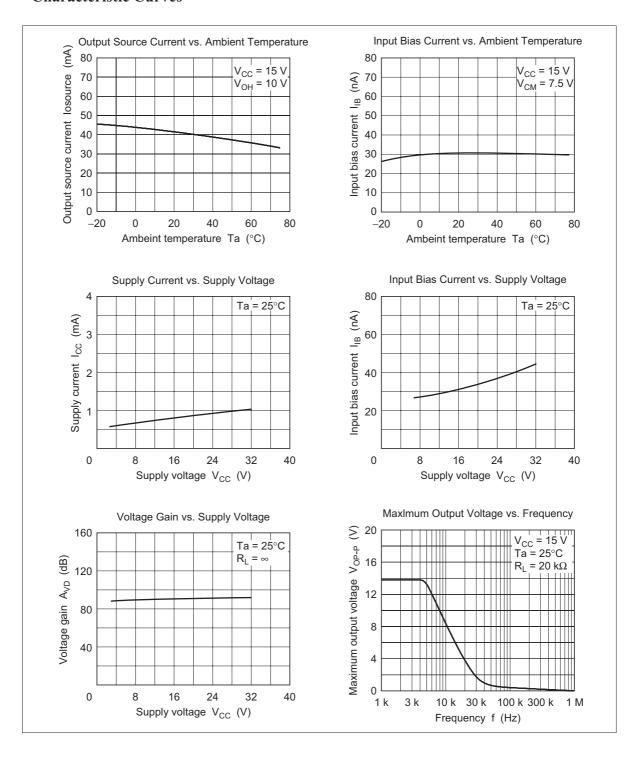
And P_cmax cannot be over the value of P_T.

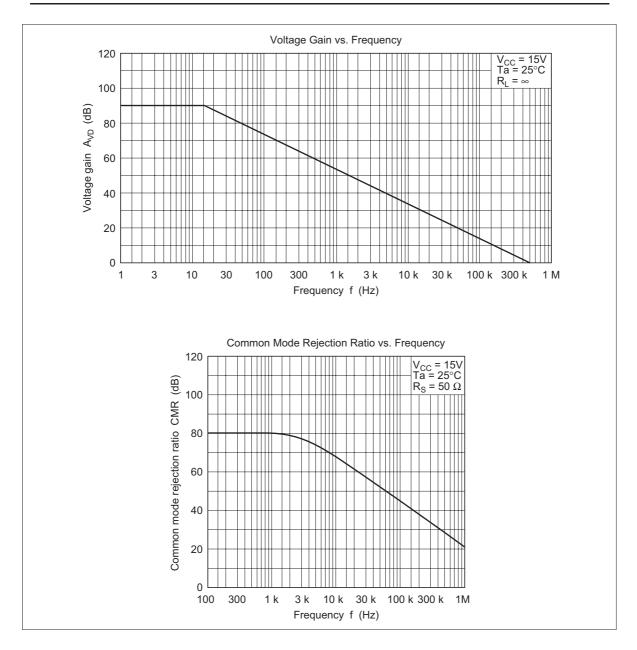


Electrical Characteristics (V $_{CC}$ = +15 V, Ta = 25 $^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input offset voltage	V _{IO}	_	2	7	mV	V_{CM} = 7.5 V, R_{S} = 50 Ω , Rf = 50 $k\Omega$
Input offset current	I _{IO}	_	5	50	nA	$V_{CM} = 7.5 \text{ V}, I_{IO} = I_{I(-)} - I_{I(+)} $
Input bias current	I _{IB}	_	30	500	nA	V _{CM} = 7.5 V
Power source rejection ratio	PSRR	_	93	_	dB	f = 100 Hz, R_s = 1 kΩ, Rj = 100 kΩ
Voltage gain	A_{VD}	75	90	_	dB	$R_{\rm S}$ = 1 k Ω , Rf = 100 k Ω , $R_{\rm L}$ = ∞
Common mode rejection ratio	CMR	_	80	_	dB	$R_s = 50 \Omega$, $Rf = 5 k\Omega$
Common mode input voltage range	V _{CM}	-0.3	_	13.5	V	R_s = 1 kΩ, Rf = 100 kΩ, f = 100 Hz
Maximum output voltage	Vop-p	_	13.6	_	V	f = 100 Hz, R _s = 1 kΩ, Rf = 100 kΩ, R _L = 20 kΩ
Output source current	losource	20	40	_	mA	$V_{IN}^{+} = 1 \text{ V}, V_{IN}^{-} = 0 \text{ V}, V_{OH} = 10 \text{ V}$
Output sink current	losink	10	20	_	mA	$V_{IN} = 0 \text{ V}, V_{IN} = 1 \text{ V}, V_{OL} = 2.5 \text{ V}$
Supply current	I _{cc}	_	8.0	2	mA	V_{IN} = GND, R_L = ∞
Slew rate	SR	_	0.19	_	V/μs	$f = 1.5 \text{ kHz}, V_{CM} = 7.5 \text{ V}, R_{L} = \infty$
Channel separation	CS	_	120	_	dB	f = 1 kHz
Output sink current	losink	15	50	_	μΑ	$V_{IN}^{+} = 0 \text{ V}, V_{IN}^{-} = 1 \text{ V}, V_{OL} = 200 \text{ mV}$
	losink	3	9	_	mA	$V_{IN}^{+} = 0 \text{ V}, V_{IN}^{-} = 1 \text{ V}, V_{OL} = 1 \text{ V}$
Output voltage	V_{OH}	13.2	13.6	_	V	$I_{OH} = -1 \text{ mA}$
	V_{OH}	12.0	13.3	_	V	$I_{OH} = -10 \text{ mA}$
Output voltage	V_{OL}	_	8.0	1.0	V	I _{OL} = 1 mA
	V_{OL}	_	1.1	1.8	V	I _{OL} = 10 mA

Characteristic Curves





Solder Mounting Method

- Small and light surface-mount packages require spicial attentions on solder mounting.
 On solder mounting, pre-heating before soldering is needed.
 The following figure show an example of infrared rays refow.
- The difference of thermal expansion coefficient between mounted substrates and IC leads may cause a
 failure like solder peeling or soler wet, and electrical characteristics may change by thermal stress.
 Therefore, mounting should be done after sufficient confirmation for especially in case of ceramic
 substrates.

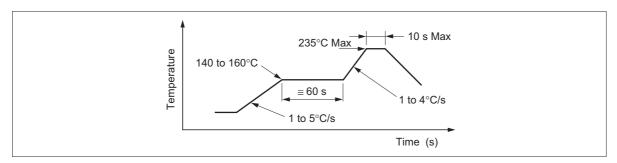
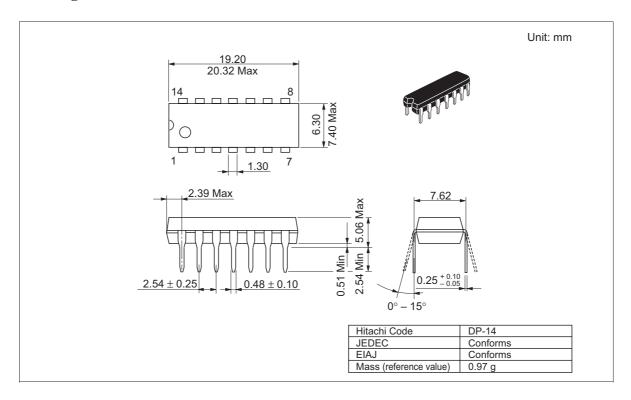
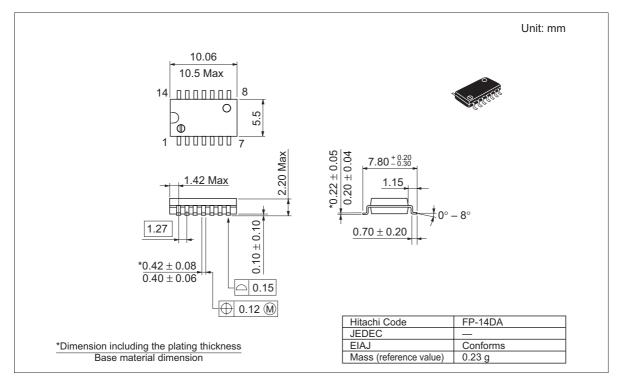


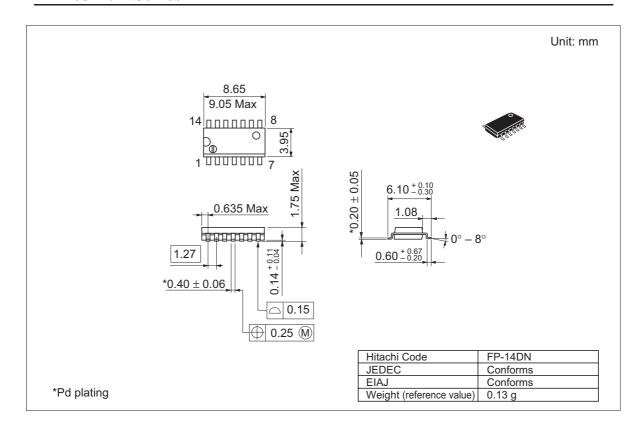
Figure 1 An Example of Infrared Rays Reflow Conditions

Package Dimensions





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